



2N7002

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	5Ω @ V _{GS} = 10V	210mA
60V	7.5Ω @ V _{GS} = 5V	170mA

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Notes 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
 A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 - https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (2N7002Q)

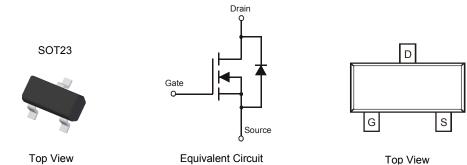
Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)



Ordering Information (Note 4)

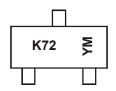
Part Number	Case	Packaging
2N7002-7-F	SOT23	3,000/Tape & Reel
2N7002-13-F	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



K72 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2002	~	2020	2021	2022	202	23 2	024	2025	2026	2027	2028
Code	N	~	Н	- 1	J	K		L	М	N	0	Р
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ			V_{DGR}	60	V
Gate-Source Voltage	V _{GSS}	±20 ±40	V		
Continuous Drain Current (Note 5) $V_{GS} = 10V$ Steady State		l _D	170 120 105	mA	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +85°C T _A = +100°C	l _D	210 150 135	mA
Maximum Continuous Body Diode Forward Current (Note 6) Continuous Pulsed			Is	0.2 0.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		-	I _{DM}	800	mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation	(Note 5)	0	370	mW	
Total Fower Dissipation	(Note 6)	P_D	540	11114	
Thermal Peciatones, Junction to Ambient	(Note 5)	_	348		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R _{eJC}	91		
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C	

Notes:

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.



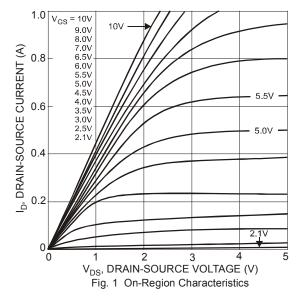
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

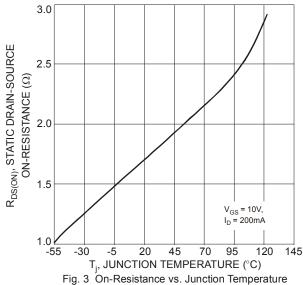
Characteristic			Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				•		•	
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _J = +25°C @ T _J = +125°C	I _{DSS}	_	_	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V _{GS(TH)}	1.0	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
	@ T _J = +25°C			3.2	7.5		V _{GS} = 5.0V, I _D = 0.05A
Static Drain-Source On-Resistance	@ T _J = +25°C @ T _J = +125°C	R _{DS(ON)}	_	2.4 4.4	5.0 13.5	Ω	$V_{GS} = 10V, I_D = 0.5A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current	<u>@ 13 - 1123 0 </u>	I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, ID = 0.5A$ $V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		grs	80	1.0		mS	V _{DS} =10V, I _D = 0.2A
Diode Forward Voltage		V _{SD}		0.78	1.5	V	$V_{GS} = 0V, I_{S} = 0.2A$
DYNAMIC CHARACTERISTICS (Note 8)		₹30		00			103 00,13 1101111
Input Capacitance		C _{iss}	_	22	50	pF	
Output Capacitance		Coss	_	11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance		C _{rss}	_	2.0	5.0	pF	T = 1.0MHZ
Gate Resistance		R_g	_	120	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)		Qg	_	223	_		
Gate-Source Charge		Q _{gs}	_	82	_	рС	V _{DS} = 10V, I _D = 250mA
Gate-Drain Charge		Q_{gd}	_	178	_		
Turn-On Delay Time		t _{D(ON)}	_	2.8	_		
Turn-On Rise Time		t _R	_	3.0	_		$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(OFF)}	_	7.6	_	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$
Turn-Off Fall Time		t⊧		5.6			NGEN ZOZZ

Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







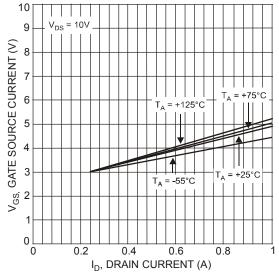
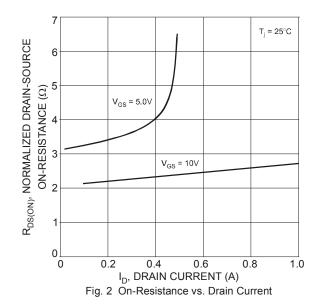
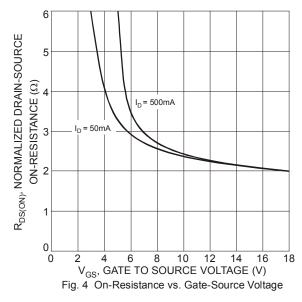


Fig. 5 Typical Transfer Characteristics





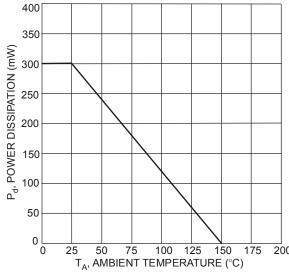


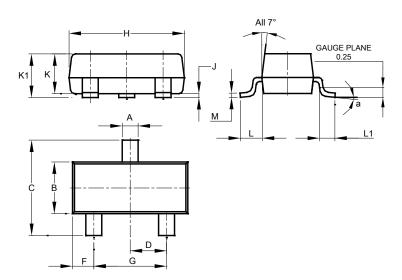
Fig. 6 Max Power Dissipation vs. Ambient Temperature



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

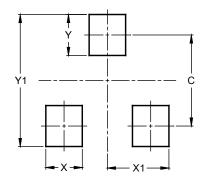


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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